

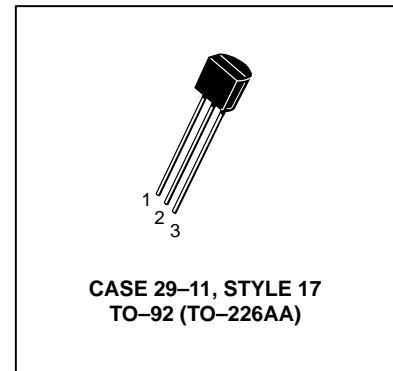
Amplifier Transistors

NPN Silicon

BC237,A,B,C
BC238B,C
BC239C

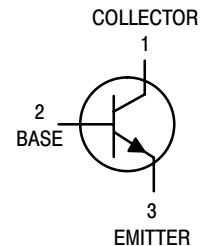
MAXIMUM RATINGS

Rating	Symbol	BC237	BC238	BC239	Unit
Collector–Emitter Voltage	V_{CEO}	45	25	25	Vdc
Collector–Emitter Voltage	V_{CES}	50	30	30	Vdc
Emitter–Base Voltage	V_{EBO}	6.0	5.0	5.0	Vdc
Collector Current — Continuous	I_C	100			mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	350			mW
		2.8			mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.0			Watts
		8.0			mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150			$^\circ\text{C}$



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	$^\circ\text{C}/\text{W}$



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 2.0\text{ mA}, I_B = 0$)	BC237 BC238 BC239	$V_{(BR)CEO}$	45 25 25	— — —	— — —	V
Emitter–Base Breakdown Voltage ($I_E = 100\ \mu\text{A}, I_C = 0$)	BC237 BC238 BC239	$V_{(BR)EBO}$	6.0 5.0 5.0	— — —	— — —	V
Collector Cutoff Current ($V_{CE} = 30\text{ V}, V_{BE} = 0$)	BC238 BC239	I_{CES}	— —	0.2 0.2	15 15	nA
($V_{CE} = 50\text{ V}, V_{BE} = 0$)	BC237		—	0.2	15	
($V_{CE} = 30\text{ V}, V_{BE} = 0$) $T_A = 125^\circ\text{C}$	BC238 BC239		— —	0.2 0.2	4.0 4.0	μA
($V_{CE} = 50\text{ V}, V_{BE} = 0$) $T_A = 125^\circ\text{C}$	BC237		—	0.2	4.0	

BC237,A,B,C BC238B,C BC239C

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
DC Current Gain ($I_C = 10\ \mu\text{A}$, $V_{CE} = 5.0\ \text{V}$)	BC237A	—	90	—	—
	BC237B/238B	—	150	—	—
	BC237C/238C/239C	—	270	—	—
($I_C = 2.0\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$)	BC237	120	—	800	—
	BC237A	120	170	220	—
	BC237B/238B	200	290	460	—
	BC237C/238C/239C	380	500	800	—
($I_C = 100\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$)	BC237A	—	120	—	—
	BC237B/238B	—	180	—	—
	BC237C/238C/239C	—	300	—	—
Collector–Emitter On Voltage ($I_C = 10\ \text{mA}$, $I_B = 0.5\ \text{mA}$) ($I_C = 100\ \text{mA}$, $I_B = 5.0\ \text{mA}$)	BC237/BC238/BC239	—	0.07	0.2	V
	BC237/BC239	—	0.2	0.6	V
	BC238	—	—	0.8	V
Base–Emitter Saturation Voltage ($I_C = 10\ \text{mA}$, $I_B = 0.5\ \text{mA}$) ($I_C = 100\ \text{mA}$, $I_B = 5.0\ \text{mA}$)		—	0.6	0.83	V
		—	—	1.05	V
Base–Emitter On Voltage ($I_C = 100\ \mu\text{A}$, $V_{CE} = 5.0\ \text{V}$) ($I_C = 2.0\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$) ($I_C = 100\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$)		—	0.5	—	V
		0.55	0.62	0.7	V
		—	0.83	—	V
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product ($I_C = 0.5\ \text{mA}$, $V_{CE} = 3.0\ \text{V}$, $f = 100\ \text{MHz}$)	BC237	—	100	—	MHz
	BC238	—	120	—	MHz
	BC239	—	140	—	MHz
($I_C = 10\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$, $f = 100\ \text{MHz}$)	BC237	150	200	—	MHz
	BC238	150	240	—	MHz
	BC239	150	280	—	MHz
Collector–Base Capacitance ($V_{CB} = 10\ \text{V}$, $I_C = 0$, $f = 1.0\ \text{MHz}$)		—	—	4.5	pF
Emitter–Base Capacitance ($V_{EB} = 0.5\ \text{V}$, $I_C = 0$, $f = 1.0\ \text{MHz}$)		—	8.0	—	pF
Noise Figure ($I_C = 0.2\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$, $R_S = 2.0\ \text{k}\Omega$, $f = 1.0\ \text{kHz}$)	BC239	—	2.0	4.0	dB
		—	—	—	dB
	BC237	—	2.0	10	dB
	BC238	—	2.0	10	dB
($I_C = 0.2\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$, $R_S = 2.0\ \text{k}\Omega$, $f = 1.0\ \text{kHz}$, $\Delta f = 200\ \text{Hz}$)	BC239	—	2.0	4.0	dB
		—	—	—	dB
	BC237	—	2.0	10	dB
	BC238	—	2.0	10	dB
	BC239	—	2.0	4.0	dB

BC237,A,B,C BC238B,C BC239C

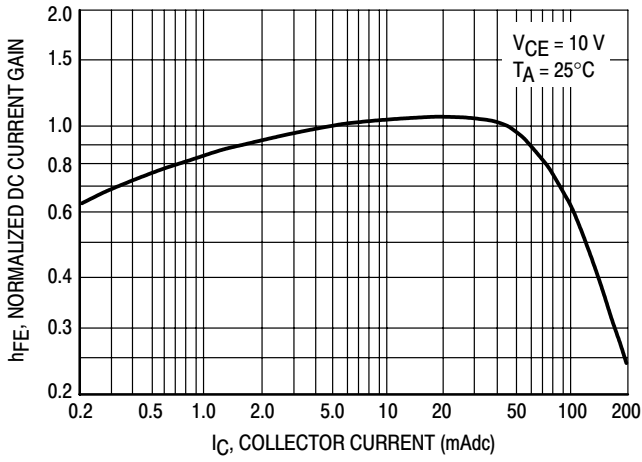


Figure 1. Normalized DC Current Gain

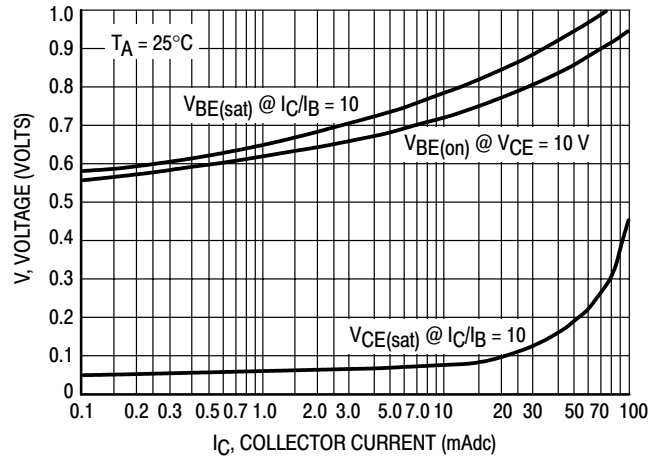


Figure 2. "Saturation" and "On" Voltages

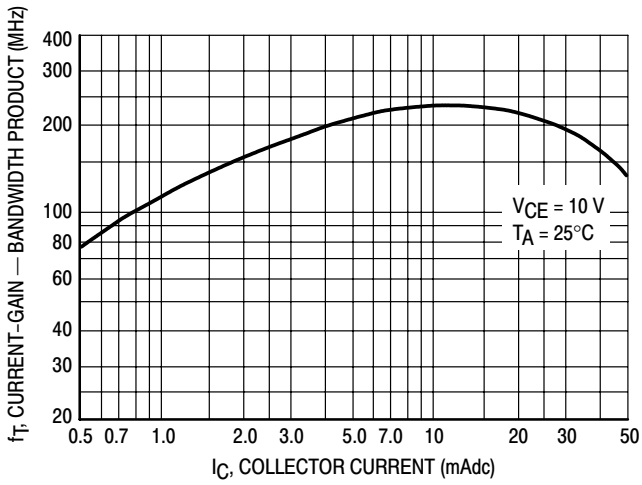


Figure 3. Current-Gain — Bandwidth Product

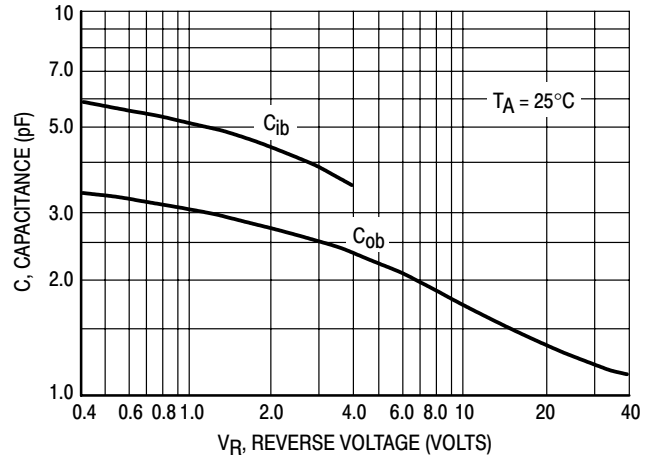


Figure 4. Capacitances

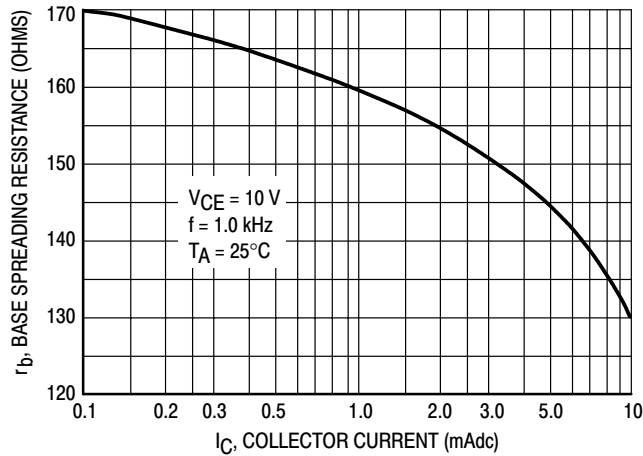
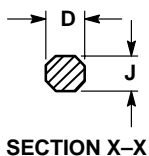
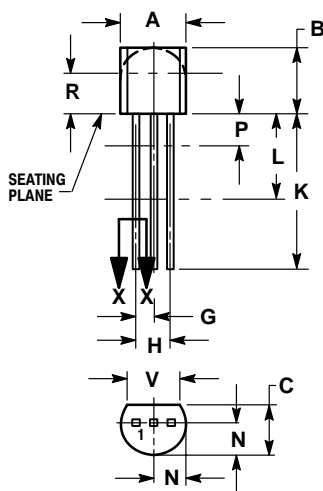


Figure 5. Base Spreading Resistance

BC237,A,B,C BC238B,C BC239C

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AL




STYLE 17:
PIN 1. COLLECTOR
2. BASE
3. EMITTER

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

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